

长电一级代理原装MOS管CJP75N80 75N80

产品名称	长电一级代理原装MOS管CJP75N80 75N80
公司名称	昆山东森微电子有限公司
价格	面议
规格参数	应用范围: 品牌:长电 型号:CJP75N80
公司地址	江苏昆山市北门路757号(office)
联系电话	86 0512 50710709 15950933050

产品详情

昆山东森微电子有限公司,专业代理电源类 功放类 led驱动类的单片机 芯片 光耦 mos管 可控硅 二极管 三极管 桥堆,原装进口,品质保证,可开增17%点增票!

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75n80 n-channel power mosfet
general description the cj75n80 uses advanced trench technology and design to provide excellent rds(on) with low gate charge. good stability and uniformity with high eas. this device is suitable for use in pwm, load switching and general purpose applications.
features advanced trench process technology
special designed for convertors and power controls
high density cell design for ultra low rds(on)
fully characterized avalanche voltage and current
fast switching
avalanche energy 100% test applications
power switching application
hard switched and high frequency circuits
uninterruptible power supply
equivalent circuit
maximum ratings (at ta=25 unless otherwise noted)
parameter symbol value unit
drain-source voltage vds 75
gate-source voltage vgs ± 25
v
drain current(dc) at tc=25 80
drain current(dc) at tc=100 id(dc) 78
drain current-continuous @current-pulsed(note1) idm(pulse) 320
apeak diode recovery voltage dv/dt 0.6 v/ns
power dissipation pd 2
wderating factor 1.13 w/ single pulsed avalanche energy(note2) eas 580 mJ
thermal resistance, junction-to-ambient 63
thermal resistance, junction-to-case 0.88 /w
operating junction and storage temperature range tj, tstg -55 ~175 notes 1. repetitive rating: pulse width limited by maximum junction temperature
2. eas condition: tj=25, vdd=50v, vg=10v, l=0.3mh, id=62a to-2201. gate2. source3. drain1 2 3
electrical characteristics (at ta=25 unless otherwise noted)
parameter symbol test condition min typ max unit
son/off states
drain-source breakdown voltage bvdss vgs = 0v, id = 250 μ a
75
gate-threshold voltage vgs(th) vds = vgs, id = 250 μ a
2.0 2.85 4.0
v
gate-body leakage current igss vds = 0v, vgs = ± 20v ± 100 nA
zero gate voltage drain current(tc=25) 1
zero gate voltage drain current(tc=125) idss vds = 75v, vgs = 0v
10 μ a
drain-source on-state resistance rds(on) vgs = 10v, id = 40a 6.5 8.0 mΩ
dynamic characteristics
forward transconductance gfs vds = 5v, id = 30a 60
sinput capacitance ciss 3100
output capacitance coss 310
reverse transfer capacitance crss vds = 25v, vgs = 0v, f = 1mhz 260
pftotal gate charge qg 100
gate-source charge qgs 18
gate-drain charge qgd vds = 30v, vgs = 10v, id = 30a 27
ncswitching timesturn-on delay time td(on) 18.2
rise time tr 15.6
turn-off delay time td(off) 70.5
fall time

tfvdd=30v,rl=15 , id=2a,vgs=10v,rg=2.5 13.8nssource-drain diode characteristicssource-drain current(body diode) isd 80pulsed source-drain current(body diode) isdm 320aforward on voltage vsd vgs =0v, isd=40a, tj=25 1.2 vreverse recovery time(note1) trr 53reverse recovery charge (note1) qrrif=75a, tj=25 ,di/dt=100a/us105nsforward turn-on time t(on) intrinsic turn-on time is negligible(turn-on dominated by ls+ld)notes1. pulse test : pulse width 300 μ s, duty cycle 1.5%,rg=2.5 ,starting tj=25

本产品的应用范围是功率，品牌是长电，型号是CJP75N80，材料是硅(Si)，封装形式是TO220